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1 TITLE OF THE INVENTION

2 **Constant Current Circuit and Active Filter Circuit Using the Same**

3 BACKGROUND OF THE INVENTION

4 Field of the Invention

5 The present invention relates generally to active filter circuits and
6 more specifically to an active filter circuit driven by a constant current circuit.

7 Description of the Related Art

8 A typical active filter circuit includes a Gm-C filter which is driven by
9 a reference current supplied from a constant current source. Usually, the
10 active filter circuit is formed on a common semiconductor substrate. Due to
11 temperature drift or variability of manufacturing process, all resistors of the
12 substrate are uniformly affected so that their resistance values deviate from
13 their rated values. This results in the reference current varying in a direction
14 opposite to the direction of deviation of all resistors. The effect of the varying
15 reference current is combined with a resistance deviation that occurs in the
16 active filter and causes a deviation of its cut-off frequency from the desired
17 frequency.

18 Japanese Patent Publication 1998-284989 discloses an active filter
19 circuit which includes a temperature-compensation current source as an extra
20 power supply unit of main DC power source. Currents produced by the DC
21 power source and the extra power supply unit are combined to drive a Gm-C
22 filter. By varying the input current of the Gm-C filter according to
23 temperature drift, the cut-off frequency of the filter is kept constant.
24 However, the use of the extra power unit for temperature compensation
25 requires the circuit designer to estimate all possible temperature variations
26 and prepare reference test data based on the estimated temperature
27 variations. The reference test data is used to adjust the output current of the
28 extra power unit corresponding to the estimated temperature variations.
29 While this prior art is satisfactory if the estimated temperature variations are
30 accurate, the disclosed technique is limited for a particular type of filters.

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1 Furthermore, the prior art is incapable of compensating for the uniformly
2 drifted variations of resistors caused by variability of manufacturing process.

3 Japanese Patent Publication 1995-321602 discloses a time-constant
4 control circuit which forms part of an active filter. The time-constant control
5 circuit is formed by a pair of transistors and a resistor coupled between the
6 emitters of the transistors. Two current sources are respectively connected to
7 the transistors. One of the transistors has its base biased at a reference
8 voltage. A variability detector is provided for detecting an RC error caused
9 by variability in the manufacturing process of integrated circuits. Based on
10 the detected RC error, a control voltage is supplied from the variability
11 detector to the base of the other transistor and the current sources. The time-
12 constant control circuit produces a control voltage that renders the
13 transconductance of the active filter unaffected by the RC error.

14 However, the prior art requires that the variability detector be
15 implemented with a Gilbert multiplication circuitry which adds to the size
16 and complexity of the integrated circuit.

17 SUMMARY OF THE INVENTION

18 It is therefore an object of the present invention to provide a simple yet
19 effective solution for compensating for uniformly drifting variations of
20 resistors of an active filter circuit formed on a common semiconductor chip,
21 regardless of varying temperature and variability of manufacturing process.

22 A further object of the present invention is to provide a constant
23 current circuit which can be universally used with an active filter for
24 compensating for uniformly drifting variations of resistors of the active filter
25 and the constant current source formed on a common semiconductor chip.

26 According to one aspect of the present invention, there is provided a
27 constant current circuit including a plurality of resistors formed on a
28 semiconductor substrate, comprising a first current source for producing a
29 first current of constant magnitude regardless of resistance variations which
30 can occur uniformly in the resistors, and a second current source for

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1 producing a second current of magnitude which is inversely variable with the
2 resistance variations. The first and second current sources are connected to
3 each other for producing an output current which is equal to a difference
4 between the first and second currents.

5 According to a second aspect, the present invention provides a
6 constant current circuit including a plurality of resistors formed on a
7 semiconductor substrate. The constant current circuit comprises a first group
8 of parallel transistors having emitters connected via respective resistors to a
9 voltage source and having collectors connected together to an output
10 terminal, a second group of parallel transistors having emitters connected via
11 respective resistors to the voltage source and having collectors connected to
12 each other, a constant current source connected between the collectors of the
13 second group of transistors and ground to produce a constant current. The
14 first and second groups of transistors have their bases connected together to
15 form a current mirror, whereby a current equal to the constant current is
16 drawn by the first group of transistors to the output terminal. Transistor-
17 resistor circuitry is provided for drawing a current inversely variable with
18 uniform resistance variations of the semiconductor substrate from the output
19 terminal to ground.

20 According to a third aspect, the present invention provides an active
21 filter circuit having a plurality of resistors formed on a semiconductor
22 substrate, comprising a first current source for producing a first current of
23 constant magnitude regardless of resistance variations which can occur
24 uniformly in the resistors, a second current source for producing a second
25 current of magnitude which is inversely variable with the resistance
26 variations, the first and second current sources being connected to each other
27 for producing an output current which is equal to a difference between the
28 first and second currents, and an active filter driven by the output current for
29 filtering an input signal.

30 According to a fourth aspect, the present invention provides an active

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1 filter circuit having a plurality of resistors formed on a semiconductor
2 substrate. The active filter circuit comprises a first group of parallel
3 transistors having emitters connected via respective resistors to a voltage
4 source and having collectors connected together to an output terminal, a
5 second group of parallel transistors having emitters connected via respective
6 resistors to the voltage source and having collectors connected to each other,
7 and a constant current source connected between the collectors of the second
8 group of transistors and ground to produce a constant current, the first and
9 second groups of transistors having their bases connected together to form a
10 current mirror, whereby a current equal to the constant current is drawn by
11 the first group of transistors to the output terminal. Transistor-resistor
12 circuitry is provided for drawing a current inversely variable with uniform
13 resistance variations of the semiconductor substrate from the output terminal
14 to ground. Further provided are a pair of switching circuits which are driven
15 by the output current for alternately assuming a conducting state according
16 to polarity of an input signal, and resistor-capacitor circuitry connected
17 across the switching circuits to produce a filtered output signal.

18 BRIEF DESCRIPTION OF THE DRAWINGS

19 The present invention will be described in detail further with reference
20 to the following drawings, in which:

21 Fig. 1 is a circuit diagram of an active filter circuit incorporating a
22 constant current source of the present invention;

23 Fig. 2 is a circuit diagram of the constant current source constructed
24 according to a first embodiment of the present invention;

25 Fig. 3 is a circuit diagram of the constant current source constructed
26 according to a second embodiment of the present invention; and

27 Fig. 4 is a circuit diagram of the constant current source constructed
28 according to a third embodiment of the present invention.

29 DETAILED DESCRIPTION

30 In Fig. 1, the active filter circuit of the present invention is comprised

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1 of a Gm-C filter 10 and a constant current source 11, both of which are
2 integrated on a common semiconductor substrate 12. Filter 10 includes a pair
3 of NPN transistors 20 and 21 whose bases are respectively coupled to input
4 terminals 31 and 32 where an input alternating voltage is applied. The
5 collectors of transistors 20, 21, which are connected to the voltage source Vcc
6 via current sources 22 and 23, are ac-coupled by a capacitor 30. The collectors
7 of these transistors 20, 21 are further connected to output terminals 34, 35
8 from which an output alternating voltage is delivered. The emitters of the
9 transistors 20, 21 are dc-coupled by a resistor 33 and further connected to the
10 collectors of NPN transistors 24, 25, respectively. The bases of transistors 24,
11 25 are connected to a circuit node 36 and the emitters of transistors 24, 25 are
12 connected to ground via respective resistors 26, 27.

13 Constant current source 11 of the present invention, which is
14 connected between the voltage source Vcc and ground, includes current
15 sources 40 and 41 and a drive circuit 42 which drives the current sources 40
16 and 41. A circuit node between the current sources 40 and 41 is connected to
17 an output terminal 43 from which an output current I_{out} is supplied to the
18 circuit node 36 of the active filter 10.

19 Details of the constant current source 11 of a first embodiment of the
20 present invention are shown in Fig. 2. In this embodiment, the drive circuit
21 42 drives the current source 40 with a current $I \times N$ and drives the current
22 source 41 with a current $I \times N/M$, where M is the number of collector-
23 coupled PNP transistors provided in each of the current source 40 and the
24 drive circuit 42 that form a current mirror and N is the number of transistors
25 provided in the current source 41 that forms part of the current mirror. In the
26 present invention, N and M are assumed to be 1 and 2, respectively.

27 Current source 40 comprises a pair of PNP transistors 50, 51 whose
28 emitters are respectively connected via resistors 52, 53 to the voltage source
29 Vcc and whose collectors connected together to the output terminal 43. Drive
30 circuit 42 comprises a pair of PNP transistors 70, 71 whose emitters are

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1 respectively connected via resistors 72, 73 to the voltage source Vcc and
2 whose collectors are connected together to a current source 74 and to the base
3 of a PNP transistor 75 whose emitter is connected to the bases of transistors
4 70, 71 and whose collector is connected to ground through a resistor 76.

5 Current source 74 is formed of resistors. These resistors are provided
6 external to the semiconductor substrate 12 so that current source 74 can
7 deliver a constant current "I", regardless of temperature drift or variability of
8 manufacturing processes which would uniformly affect the resistivity of all
9 the internally provided resistors of the substrate 12.

10 The bases of PNP transistors 50, 51 of current source 40 and the bases
11 of transistors 70, 71 of driver 42 are connected together to form a current
12 mirror and the PNP transistor 60 forms part of the current mirror by coupling
13 its base to the bases of transistors 50, 51, 70, 71. As a result of the current
14 mirror relation, the same current I is caused to flow through the collector-
15 coupled PNP transistors 50, 51 of current source 40 to the output terminal 43
16 as the current I drawn through the collector-coupled PNP transistors 70, 71
17 by the constant current source 74 to ground.

18 Current source 41 is of a V_{BE} -dependent type. Current source 41
19 includes a PNP transistor 60 whose base is connected to the bases of
20 transistors 50, 51, 70, 71. The emitter of transistor 60 is connected to the
21 voltage source Vcc via a resistor 61 and its collector is connected to a circuit
22 node N1 to which the base of an NPN transistor 62 and the collector of an
23 NPN transistor 63 are connected. The emitter of transistor 62 and the base of
24 transistor 63 are connected together to a circuit node N2 which is grounded
25 via a resistor 65. The collector of transistor 62 is connected to the output
26 terminal 43. The emitter of transistor 63 is connected to ground via a resistor
27 64.

28 In the current source 41, the PNP transistor 60 draws a current from
29 the voltage source Vcc to ground via transistor 63 and resistor 64. Since the
30 number of PNP transistors provided in the current source 41 is 1/2 of the

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1 PNP transistors of each half of the current mirror circuit, the current that
 2 flows through the node N1 is one-half of the current I.
 3 NPN transistors 62 and 63 cause a current I_1 to flow from the output
 4 terminal 43 to ground through resistor 65. This current is given by Equation
 5 (1).

$$6 \quad I_1 = \frac{V_{N2}}{R_5} \quad (1)$$

7 where, V_{N2} is the potential at the circuit node N2 and R_5 is the value of
 8 resistor 65. Since the potential V_{N2} is expressed as follows:

$$9 \quad V_N = V_{BE} + \frac{N}{M} I \times R_4 \quad (2)$$

10 Since $N = 1$ and $M = 2$, Equation (2) is rewritten as:

$$11 \quad V_{N2} = V_{BE} + \frac{1}{2} I \times R_4 \quad (3)$$

12 where, V_{BE} is the base-emitter voltage of transistor 63 and R_4 is the value of
 13 resistor 64. Current I_1 is thus given by Equation (4).

$$14 \quad I_1 = \frac{V_{BE} + \frac{1}{2} I \times R_4}{R_5} \quad (4)$$

15 Since the output current I_{out} is equal to the difference between I and I_1 , the
 16 following relation holds:

$$17 \quad I_{out} = I - I_1 = I - \frac{V_{BE} + \frac{1}{2} I \times R_4}{R_5} \quad (5)$$

18 When the current I_{out} is supplied to the node 36 of active filter 10, the
 19 NPN transistors 24 and 25 are turned ON. If an input alternating voltage is
 20 applied to the terminals 34 and 35, the NPN transistors 20 and 21 are turned
 21 ON and OFF in a complementary fashion depending on the polarity of the
 22 input voltage. As a result, when the transistor 20 is ON, it draws a current
 23 from the current source 22 to ground through transistor 24 and resistor 26,
 24 and when the transistor 21 is ON, it draws a current from the current source

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1 23 to ground through transistor 25 and resistor 27.

2 If the input voltage is a low frequency signal, the capacitor 30
3 functions as a high impedance element and its presence can be ignored.
4 Hence, the output terminals 34 and 35 are in an open circuit condition,
5 causing an alternating voltage to appear thereacross. If the input voltage is a
6 high frequency signal, the capacitor 30 functions as a low impedance element.
7 Hence, the output terminals 34 and 35 are in a short-circuit condition, causing
8 no output voltage to appear thereacross. In this way, the active filter 10
9 operates as a low-pass filter. The cut-off frequency f_c of the low-pass filter is
10 given by Equation (6).

$$11 \quad f_c = \frac{1}{2\pi \sqrt{C \times \frac{1}{g_m}}} \quad (6)$$

$$12 \quad g_m = \frac{1}{R + \frac{2 \times V_{cc}}{I_{out}}} \quad (7)$$

13 where C is the capacitance of capacitor 30, R is the value of resistor 33, and
14 V_{cc} is the power voltage of the voltage source Vcc.

15 Current I_1 of Equation (4) varies inversely with resistance variations
16 which can occur uniformly in all internal resistors of the semiconductor
17 substrate 12 as follows.

18 If the temperature of semiconductor substrate 12 rises, all resistors on
19 the substrate 12 increase uniformly, and the current I_1 of current source 41
20 decreases, while current I of current source 74 remains unaffected due to the
21 provision of resistors external to the substrate 12. Because of the current
22 mirror relation to the drive circuit 42, the current I drained through the
23 current source 40 to the output terminal 43 is also unaffected. Therefore, the
24 output current I_{out} increases as seen from Equation (5). This increase would
25 cause the transconductance g_m to decrease. However, Equation (7) shows
26 that a concomitant increase in the resistance R (of resistor 33) produces an

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1 opposing effect on this decrease. On the other hand, if the temperature of
2 substrate 12 lowers, all of its resistors decrease uniformly and the current I_1
3 increases while the output current I_{out} decreases, tending to increase the
4 transconductance. A concomitant decrease in the resistance R counteracts
5 this increase in transconductance. If the resistance R is appropriately
6 determined in relation to the output current I_{out} , such temperature-
7 dependent mutual-conductance variations can be completely nullified, so
8 that the cut-off frequency f_c can be maintained constant under a varying
9 temperature.

10 Active filter 10 and the constant current source 11 cooperate in much
11 the same way when all the internal resistors of the substrate 12 are caused to
12 offset uniformly from their nominal values due to variability of
13 manufacturing processes.

14 The present invention thus eliminates the need to prepare reference
15 measurement data for circuit testing. Therefore, the constant current source
16 11 of the present invention can be universally used with various active filters.

17 A constant current source 11A, shown in Fig. 3, is a second
18 embodiment of the present invention. This embodiment differs from the
19 previous embodiment in that it replaces the V_{BE} -dependent type current
20 source 41 with a V_{CC} -dependent type current source 41A.

21 Current source 41A includes an NPN transistor 81 whose collector is
22 connected to the output terminal 43. The base of transistor 81 is connected to
23 a circuit node N3 of resistors 82 and 83 connected in series between V_{cc} and
24 ground. Transistor 81 has its emitter coupled to ground through a resistor 84.
25 The potential at node N3 is given by Equation (8) and the transistor 81 draws
26 a current I_2 from the output terminal 43 to ground. Current I_2 is given by
27 Equation (9).

$$28 \quad V_{N3} = \frac{R_{13}}{R_{12} + R_{13}} \times V_{cc} \quad (8)$$

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$$1 \quad I_2 = \frac{V_{N3} - V_{BE}}{R_{14}} = \frac{R_{13} \times V_{cc}}{(R_{12} + R_{13})R_{14}} - \frac{V_{BE}}{R_{14}} \quad (9)$$

2 where, R_{12} , R_{13} and R_{14} represent the resistances of resistors 82, 83 and 84,
 3 respectively, and V_{BE} is the base-emitter voltage of transistor 81. Therefore,
 4 the output current I_{out} is obtained as follows:

$$5 \quad I_{out} = I - I_2 = I - \left\{ \frac{R_{13} \times V_{cc}}{(R_{12} + R_{13})R_{14}} - \frac{V_{BE}}{R_{14}} \right\} \quad (10)$$

6 It is seen from Equations (9) and (10) that when all resistors of the
 7 substrate 12 uniformly increase, current I_2 decreases and output current I_{out}
 8 increases, and when all resistors uniformly decrease, current I_2 increases and
 9 output current I_{out} decreases. The cut-off frequency of the filter 10 is thus
 10 maintained constant.

11 A constant current source 11B, shown in Fig. 4, is a third embodiment
 12 of the present invention, which differs from the first embodiment in that it
 13 replaces the V_{BE} -dependent type current source 41 with a band-gap type
 14 current source 41B.

15 Current source 41B includes a pair of PNP transistors 90 and 91 having
 16 their base connected to the bases of current-mirror transistors 50, 51, 70, 71,
 17 and having their emitters connected to V_{cc} via resistors 92 and 93. The
 18 collector of transistor 90 is connected to the collectors of a group G of "n"
 19 parallel transistors of NPN conductivity, while the collector of transistor 91 is
 20 coupled to a circuit node N5 to which the collector of an NPN transistor 94
 21 are also connected.

22 The emitters of transistor group G are connected together to a point
 23 which is connected through resistors 96 and 97 to ground, while the emitter of
 24 transistor 94 is connected to a circuit node N4 which is formed between the
 25 resistors 96 and 97. Current source 41B further includes an NPN transistor 95
 26 whose collector is connected to the output terminal 43, its emitter being
 27 coupled through a resistor 99 to ground. The bases of transistors 94, 95 and

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1 transistor group G are connected together to the circuit node N5. PNP
 2 transistors 90 and 91 constitute a current mirror with the PNP transistors 50,
 3 51, 70 and 71. Since the PNP transistors 90 and 91 have their collectors not
 4 coupled together unlike transistors 50, 51 and 70, 71, one-half of the current I
 5 is drawn through each of the transistors 90 and 91 to the circuit node N4,
 6 where these currents are summed to produce a current I through the resistor
 7 97. Therefore, the potentials V_{N4} and V_{N5} at the circuit nodes N4 and N5 are
 8 given by Equations (11) and (12), respectively.

$$9 \quad V_{N4} = I \times R_{17} \quad (11)$$

$$10 \quad V_{N5} = V_{N4} + V_{BE} = V_{N4} + \frac{I \times R_{16}}{2} + V_{GBE} \quad (12)$$

11 where, R_{16} and R_{17} are the respective resistances of resistors 96 and 97, V_{BE} is
 12 the base-emitter voltage of transistor 94 and V_{GBE} is the base-emitter voltage
 13 of the transistor group G.

14 According to bipolar transistor theory, V_{GBE} of the "n" transistors
 15 connected in parallel to transistor 94, is given by Equation (13).

$$16 \quad V_{GBE} = V_{BE} - V_T \times \ln(n) \quad (13)$$

17 where, V_T is the volt equivalent of temperature which is expressed as:

$$18 \quad V_T = \frac{k \times T}{q} \quad (14)$$

19 where k is the Boltzmann constant, T is the absolute temperature (Kelvin) and
 20 q is the electric charge. From Equations (12) and (13), the voltage developed
 21 across the resistor 96 is equal to:

$$22 \quad \frac{1}{2} I \times R_{16} = V_{BE} - V_{GBE} = V_T \times \ln(n) \quad (15)$$

23 Hence, the potentials V_{N4} and V_{N5} are given by Equations (16) and (17),
 24 respectively.

$$25 \quad V_{N4} = \{2 \times V_T \times \ln(n)\} \times \frac{R_{17}}{R_{16}} \quad (16)$$

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$$V_{N5} = V_{BE} + \{2 \times V_T \times \ln(n)\} \times \frac{R_{17}}{R_{16}} \quad (17)$$

The first term of Equation (17), i.e., V_{BE} indicates that the potential V_{N5} varies with a negative temperature characteristic and the second term, i.e., $\{2 \times V_T \times \ln(n)\}$ indicates that it varies with a positive temperature characteristic, which counteracts the negative temperature characteristic of the first term. The potential V_{N5} at the circuit node N5 is thus kept constant regardless of temperature variations. Since current I_3 , which is drawn by transistor 95 to pass through resistor 99 to ground, is given by:

$$I_3 = \frac{V_{N5} - V_{BE}}{R_{19}} \quad (18)$$

(where, V_{BE} is the base-emitter voltage of transistor 95 and R_{19} is the value of resistor 99), the output current I_{out} of Fig. 4 becomes:

$$I_{out} = I - I_3 = I - \frac{V_{N5} - V_{BE}}{R_{19}} \quad (19)$$

It is seen from Equations (18) and (19) that current I_3 varies inversely with resistance variations and the output current I_{out} varies with the resistance variations.